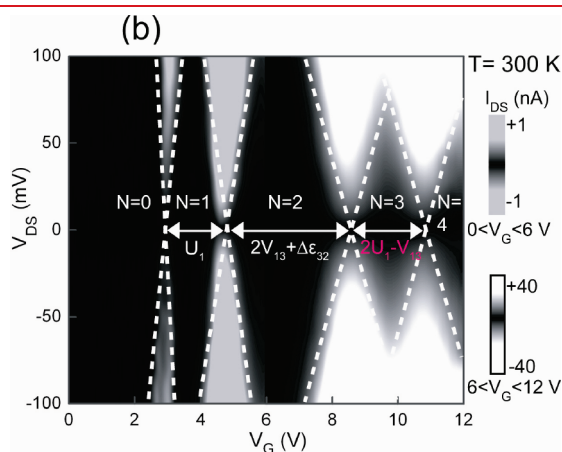
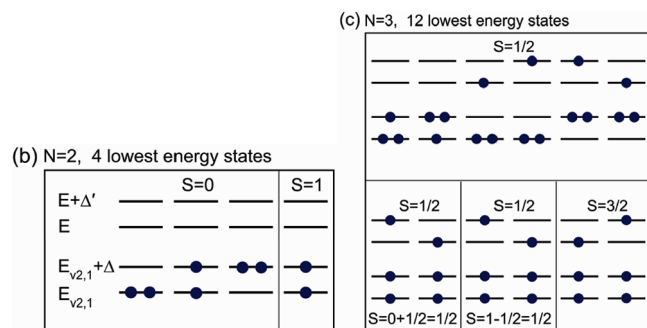


**Room-Temperature Charge Stability Modulated by Quantum Effects in a Nanoscale Silicon Island** [*Nano Letters* **2011**, *11*, 1591–1597 DOI: 10.1021/nl1044692]. S. J. Shin, J. J. Lee, H. J. Kang, J. B. Choi,\* S.-R. Eric Yang, Y. Takahashi, and D. G. Hasko

The vertical indexing of the current grayscale in inset (b) of Figure 4 is incorrect in the original article;  $0 < V_G < 12$  V should be corrected to  $6 < V_G < 12$  V. In addition, the value of spin  $S = 1/2$  in the legend of Figure 5b is incorrect;  $S = 1/2$  should be corrected to  $S = 0$ . Finally, electronic occupation configurations of lower panels in Figure 5c are incorrect. Their correct versions are reproduced below. No changes to the figure captions and their respective text are required. None of the results and conclusions of the article are affected by these corrections.



**Figure 4.** inset (b): The calculated addition charging energies, approximately  $U_1 \approx 0.38$  eV,  $2V_{13}\epsilon - \epsilon_2 \approx 0.9$  eV, and  $V_{13} + 2(U_1 - V_{13}) \approx 0.46$  eV (for  $N = 1 \rightarrow 2$ ,  $2 \rightarrow 3$ , and  $3 \rightarrow 4$ , respectively) are denoted by arrows in inset (b), which are in the same range as those of the charge stability data observed at 300 K.



**Figure 5.** (b and c) Electronic occupation configurations illustrating the number of lowest energy states for (b)  $N = 2$  and (c)  $N = 3$ . Note that due to many-body exchange interactions states with the same  $\{n_i\}$  but with different  $S$  do not have the same energy.

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